

# 深圳市晶泰源电子有限公司

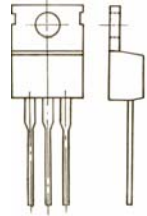
## 2SD880 TRANSISTOR (NPN)

### FEATURES

- Low frequency power amplifier
- Complement to 2SB834

### TO-220

1. BASE
2. COLLECTOR
3. EMITTER



1 2 3

### MAXIMUM RATINGS ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current -Continuous	3	A
$P_C$	Collector Power Dissipation	1.5	W
$T_J$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=50\text{mA}$ , $I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	7			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}$ , $I_E=0$			100	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=7\text{V}$ , $I_C=0$			100	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=5\text{V}$ , $I_C=500\text{mA}$	60		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3\text{A}$ , $I_B=300\text{mA}$			1	V
Base-emitter voltage	$V_{BE}$	$I_C=0.5\text{A}$ , $V_{CE}=5\text{V}$			1	V
Transition Frequency	$f_T$	$V_{CE}=5\text{V}$ , $I_C=500\text{mA}$		3		MHz
Collector output capacitance	$C_{ob}$	$V_{CB}=10\text{V}$ , $I_E=0$ , $f=1\text{MHz}$		70		pF
Turn on time	$t_{on}$	$I_{B1}=-I_{B2}=0.2\text{A}$ , $I_C=2\text{A}$ $V_{CC}=30\text{V}$ , $PW=20\mu\text{s}$		0.8		$\mu\text{s}$
Storage time	$t_s$			1.5		$\mu\text{s}$
Fall time	$t_f$			0.8		$\mu\text{s}$

### CLASSIFICATION OF $h_{FE}$

Rank	O	Y	GR
Range	60-120	100-200	150-300